

CLEANING SOLUTION AND METHOD OF CLEANING A SEMICONDUCTOR DEVICE
USING THE SAME

ABSTRACT OF THE DISCLOSURE

5 In a cleaning solution and a method of cleaning a semiconductor substrate, the cleaning
solution includes about 1 to about 10 percent by weight of sulfuric acid, about 0.5 to about 5
percent by weight of aqueous hydrogen peroxide solution, and about 85 to about 98.5 percent
by weight of hydrogen fluoric acid solution. Various polymers attached to a metal wiring
formed on a substrate are removed by immersing the substrate into the cleaning solution. The
10 substrate is rinsed to remove the cleaning solution remaining on the substrate. Thus, the
polymers can be completely removed without damage to the metal wiring and an underlying
oxide film.